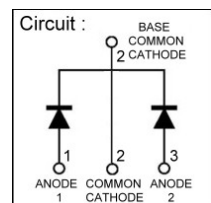
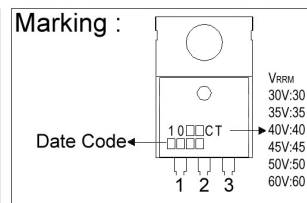
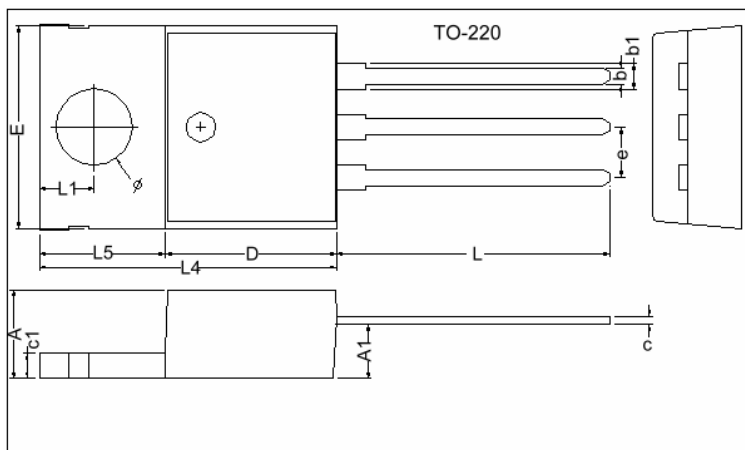


GESBL1030CT~1060CT**SCHOTTKY BARRIER RECTIFIERS****REVERSE VOLTAGE 30V TO 60V, CURRENT 10A****Description**

The GESBL1030CT~1060CT are designed for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

Features

- Guard ring for transient protection
- Low power loss, high efficiency
- High current capability, low V_F
- High surge capacity

Package Dimensions

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.40	4.80	c1	1.25	1.45
b	0.76	1.00	b1	1.17	1.47
c	0.36	0.50	L	13.25	14.25
D	8.60	9.00	e	2.54 REF.	
E	9.80	10.4	L1	2.60	2.89
L4	14.7	15.3	Ø	3.71	3.96
L5	6.20	6.60	A1	2.60	2.80

Maximum Ratings and Electrical Characteristics at $T_a=25^\circ\text{C}$ unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%

Parameters	Symbol	Ratings						Unit
		GESBL 1030CT	GESBL 1035CT	GESBL 1040CT	GESBL 1045CT	GESBL 1050CT	GESBL 1060CT	V
Max. Recurrent Peak Reverse Voltage	V_{RRM}	30	35	40	45	50	60	V
Max. RMS Voltage	V_{RMS}	21	24.5	28	31.5	35	42	V
Max. DC Blocking Voltage	V_{DC}	30	35	40	45	50	60	V
Max. Average Forward Rectified Current (See Fig.1) @ $T_C=95^{\circ}C$	$I_{(AV)}$	10						A
Peak Surge Forward Current 8.3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	125						A
Max. Forward Voltage @ 5A (Note 1)	V_F	0.55				0.7		V
Max. DC Reverse Current At Rated DC Blocking Voltage @ $T_J=25^{\circ}C$ @ $T_J=100^{\circ}C$	I_R	0.5 50						mA
Typical Thermal Resistance (Note 2)	$R_{\theta JC}$	3.0						$^{\circ}C/W$
Operating Temperature Range	T_j	-55 ~ +125						$^{\circ}C$
Storage Temperature Range	T_{stg}	-55 ~ +150						$^{\circ}C$

Notes: 1. 300us Pulse Width, 2% Duty Cycle.

2. Thermal Resistance Junction to Case.

Characteristics Curve

Fig. 1 Forward Current Derating Curve

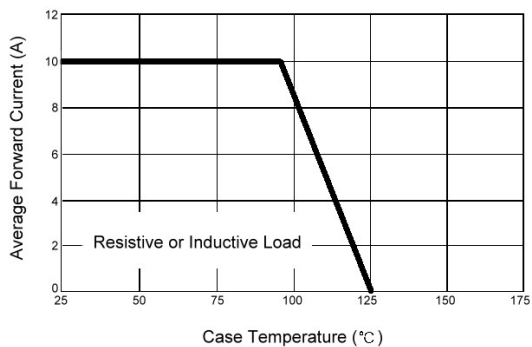


Fig. 2 Maximum Non-Repetitive Surge Current

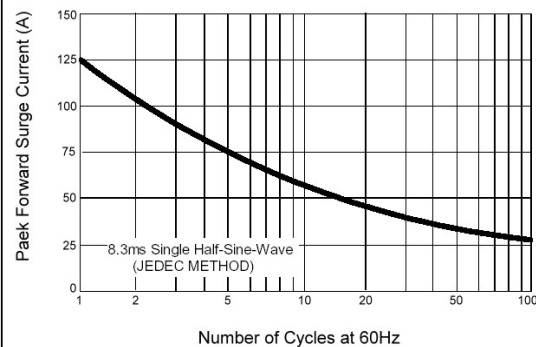


Fig. 3 Typical Reverse Characteristics

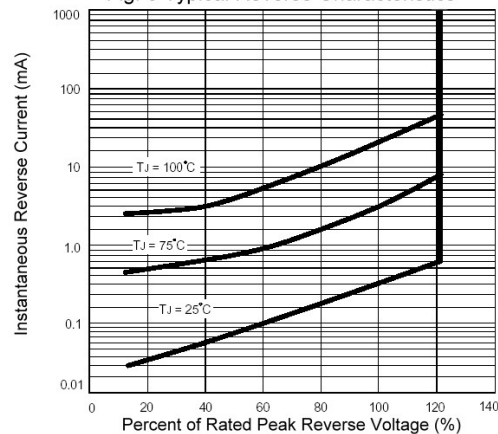


Fig. 4 Typical Forward Characteristics

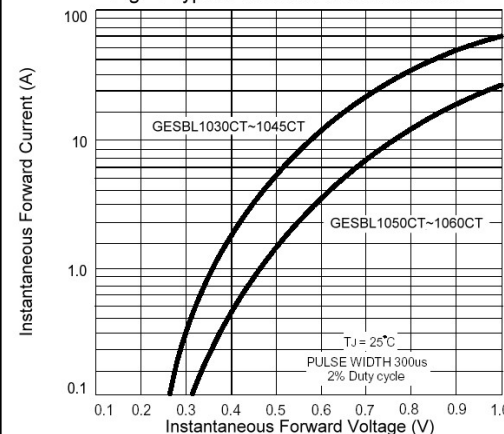
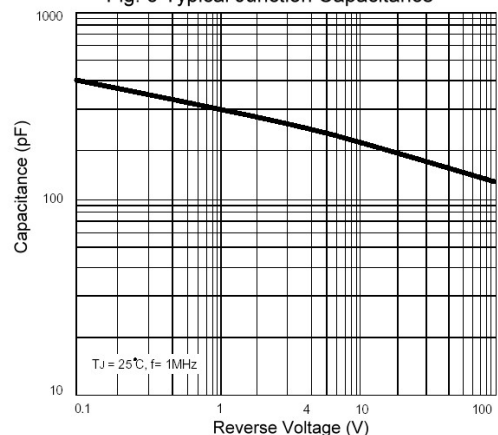


Fig. 5 Typical Junction Capacitance



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